

<b>Notice of References Cited</b>				Application No. <b>08/799,506</b>		Applicant(s) <b>Yamazaki et al.</b>	
				Examiner <b>M. Wilczewski</b>		Group Art Unit <b>1107</b>	

  

U.S. PATENT DOCUMENTS						
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
	A	4,475,027	10/1984	Pressley	----	----
	B	5,304,357	4/1994	Sato et al.	----	----
	C					
	D					
	E					
	F					
	G					
	H					
	I					
	J					
	K					
	L					
	M					

  

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
	N	2-73623	3/1990	JP	Aoyama et al.	----	----
	O	1-76715	3/1989	JP	Sera	----	----
	P	3-286518	12/1991	JP	Hashizume	----	----
	Q	4-307727	10/1992	JP	Hashizume	----	----
	R	2-255292	10/1990	JP	Imamura	----	----
	S						
	T						

  

NON-PATENT DOCUMENTS		
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
U	Wagner et al., "Formation of p-n Junctions and Silicides in Silicon Using a High Performance Laser Beam Homogenization System", Applied Surface Science, Vol. 43, 1989, pp. 260-263.	1989
V	Jhon et al., "Crystallization of Amorphous Silicon by Excimer Laser Annealing With a Line Shape Beam Having a Gaussian Profile", Jpn. J. Appl. Phys., Vol. 33, 1994, pp. L1438-L1441.	1994
W		
X		